

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ~~manufacturing~~ method for manufacturing a substrate used for a liquid crystal device by slant vacuum deposition ~~oblique evaporation~~ of an inorganic material on an underlayer having a gap section on ~~the surface~~ a surface formed on the substrate so as to ~~form the~~ form an inorganic alignment layers, ~~comprising the steps of:~~ layer, comprising:

a first ~~oblique evaporation step by unidirectional oblique evaporation of~~ slant vacuum deposition step of disposing the inorganic material unidirectionally on the substrate ~~on which the underlayer having the gap section is formed on the surface of~~ formed on the substrate so as to form ~~the first~~ a first inorganic ~~oblique evaporation layer 36a;~~ slant vacuum deposition layer;

a second ~~oblique evaporation~~ slant vacuum deposition step by ~~oblique evaporation of~~ disposing the inorganic material on the substrate unidirectionally, a direction in the second slant vacuum deposition step having an ~~from at least a different azimuth angle inside the substrate from the oblique evaporation direction of the inorganic material in the first oblique evaporation step~~ different from at least an azimuth angle of the first slant vacuum deposition step so as to form ~~the second oblique evaporation layer 36b in an area close to a~~ second inorganic slant vacuum deposition layer near the gap section and on the first inorganic ~~oblique evaporation layer.~~ slant vacuum deposition layer, wherein the direction for disposing the inorganic material unidirectionally in the first or the second slant vacuum deposition step is along a longitudinal direction of the gap section.

2. (Currently Amended) A ~~manufacturing~~ The method for manufacturing a substrate ~~the substrate used for a~~ the liquid crystal device, device according to claim 1, ~~wherein~~

the azimuth angle of the ~~oblique evaporation direction~~ (S_A) of the ~~inorganic material in first~~
~~slant vacuum deposition~~ the first ~~oblique evaporation step~~ and the azimuth angle of the
~~oblique evaporation direction~~ (S_B) of the ~~inorganic material in the second oblique evaporation~~
~~step differs~~ ~~slant vacuum deposition step differing~~ by nearly 90 degrees.

3. (Currently Amended) ~~A manufacturing~~ The method of a
~~substrate manufacturing the substrate used for a~~ the liquid crystal device according to claim 1,
~~wherein:~~

~~deposition a deposition~~ angle (θ_1) between the ~~oblique evaporation direction of~~
~~the for disposing the~~ inorganic material in the first ~~oblique evaporation~~ slant vacuum
deposition step and the substrate ~~is in being in~~ the range of 5 to 10 degrees;

~~deposition a deposition~~ angle (θ_2) between the ~~oblique evaporation direction of~~
~~the for disposing the~~ inorganic material in the second ~~oblique evaporation~~ slant vacuum
deposition step and the substrate ~~is in being in~~ the range of 25 to 30 degrees.

4. (Currently Amended) ~~A manufacturing~~ The method for a of manufacturing the
~~substrate used for a the liquid crystal device,~~ device according to claim 1, wherein the a slant
vacuum deposition ~~oblique evaporation direction~~ (S_A, S_B) ~~is being~~ selected according to a
construction and disposition of the gap ~~section (80)~~ section formed on ~~the surface~~ a surface of
the underlayer ~~in the oblique evaporation of inorganic material in~~ at least one of the first
~~oblique evaporation~~ slant vacuum deposition step and the second ~~oblique evaporation~~ slant
vacuum deposition step.

5. (Currently Amended) ~~A manufacturing~~ The method of manufacturing for a the
~~substrate used for a the liquid crystal device,~~ device according to claim 1, wherein:

the thickness of ~~the inorganic~~ the first inorganic slant vacuum deposition
~~oblique evaporation~~ layer formed in the first ~~oblique evaporation~~ slant vacuum deposition step
is in the range of 5 nm to 16 nm; and

the thickness of the second inorganic slant vacuum deposition ~~the inorganic~~
~~oblique evaporation~~ layer formed in the second ~~oblique evaporation~~ slant vacuum deposition
step is in the range of 10 nm to 40 nm.

6. (Currently Amended) ~~A manufacturing~~ The method for a substrate of
manufacturing the substrate used for a the liquid crystal device, device according to claim 1,
~~wherein the inorganic material is silicon~~ being silicon oxide.